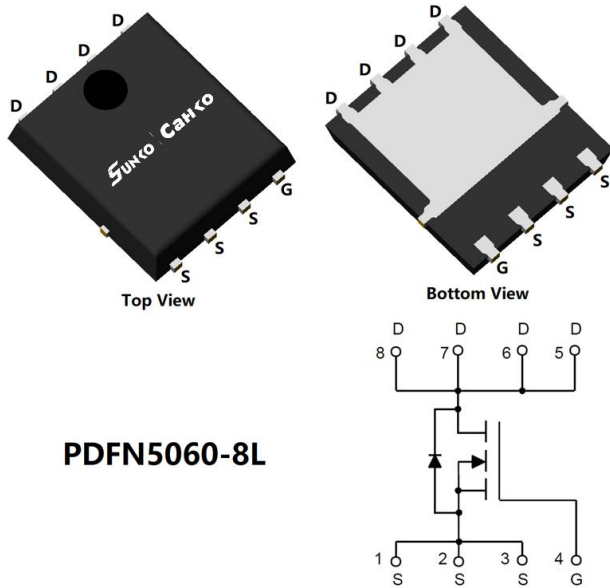


N-Channel Enhancement Mode Field Effect Transistor



Product Summary

- V_{DS} 60V
- I_D 95A
- $R_{DS(ON)}$ (at $V_{GS}=10V$) <2.5 mohm
- $R_{DS(ON)}$ (at $V_{GS}=4.5V$) <3.4 mohm
- 100% EAS Tested
- 100% ∇V_{DS} Tested

General Description

- Split Gate Trench MOSFET technology
- Excellent package for heat dissipation
- High density cell design for low $R_{DS(ON)}$
- Moisture Sensitivity Level 1
- Epoxy Meets UL 94 V-0 Flammability Rating
- Halogen Free

Applications

- DC-DC Converters
- Power management functions
- Synchronous-rectification applications

■ Absolute Maximum Ratings ($T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-source Voltage		V_{DS}	60	V
Gate-source Voltage		V_{GS}	± 20	V
Drain Current (Silicon limited)		I_D	155	A
Drain Current ^A	$T_C=25^\circ\text{C}$	I_D	95	A
	$T_C=100^\circ\text{C}$		60	
Pulsed Drain Current ^B		I_{DM}	390	A
Avalanche energy ^C		E_{AS}	500	mJ
Total Power Dissipation ^D		P_D	120	W
Thermal Resistance Junction-to-Case		$R_{\theta JC}$	1.04	$^\circ\text{C/W}$
Thermal Resistance Junction-to-Ambient ^E		$R_{\theta JA}$	20	
Junction and Storage Temperature Range		T_J, T_{STG}	$-55 \sim +150$	$^\circ\text{C}$

■ Ordering Information (Example)

PREFERRED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
SCG95G06A	F1	SCG95G06A	5000	10000	50000	13" reel

SCG95G06A

■ Electrical Characteristics (T_j=25℃ unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} = 0V, I _D =250μA	60			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =60V,V _{GS} =0V			1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} = ±20V, V _{DS} =0V			±100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D =250μA	1.2	1.6	2.5	V
Static Drain-Source On-Resistance	R _{DS(on)}	V _{GS} = 10V, I _D =20A		2.1	2.5	mΩ
		V _{GS} = 4.5V, I _D =15A		2.7	3.4	
Diode Forward Voltage	V _{SD}	I _S =20A,V _{GS} =0V			1.2	V
Maximum Body-Diode Continuous Current	I _S				95	A
Dynamic Parameters						
Input Capacitance	C _{iss}	V _{DS} =25V,V _{GS} =0V,f=100KHZ		5950		pF
Output Capacitance	C _{oss}			1250		
Reverse Transfer Capacitance	C _{rss}			85		
Switching Parameters						
Total Gate Charge	Q _g	V _{GS} =10V,V _{DS} =50V,I _D =50A		93		nC
Gate-Source Charge	Q _{gs}			17		
Gate-Drain Charge	Q _{gd}			14		
Reverse Recovery Chrage	Q _{rr}	I _F =25A, di/dt=100A/us		73		ns
Reverse Recovery Time	t _{rr}			68		
Turn-on Delay Time	t _{d(on)}	V _{GS} =10V,V _{DD} =30V,I _D =25A R _{GEN} =2Ω		22.5		
Turn-on Rise Time	t _r			6.7		
Turn-off Delay Time	t _{d(off)}			80.3		
Turn-off fall Time	t _f			26.9		

Note:

- The maximum current rating is package limited.
- Repetitive rating; pulse width limited by max. junction temperature.
- V_{DD}=50 V, R_G=25 Ω, L=0.5mH, starting T_j=25 °C.
- P_D is based on max. junction temperature, using junction-case thermal resistance.
- The value of R_{θJA} is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with Ta=25 °C.

■ Typical Performance Characteristics

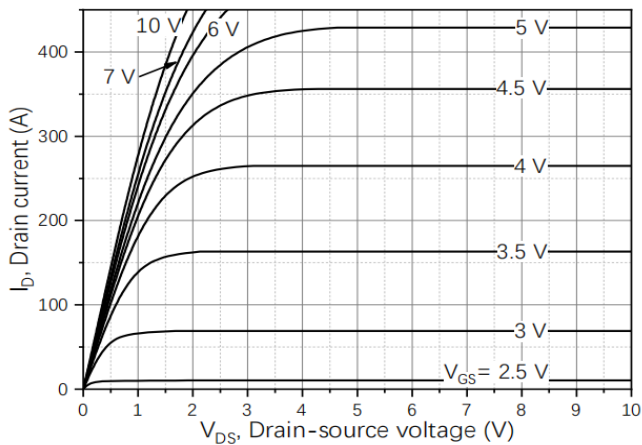


Figure1. Output Characteristics

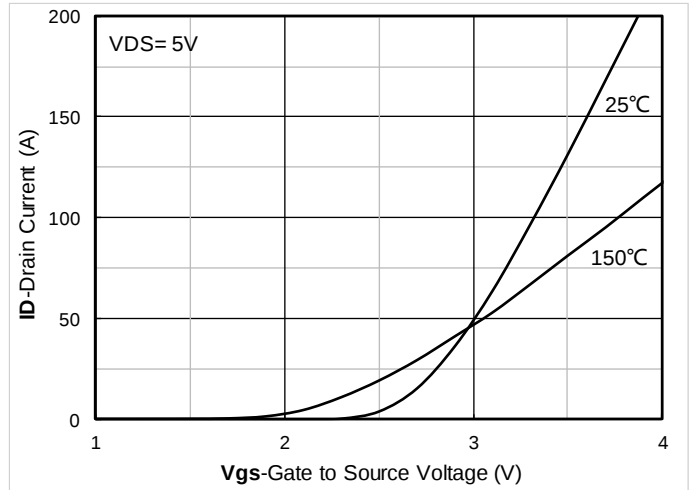


Figure2. Transfer Characteristics

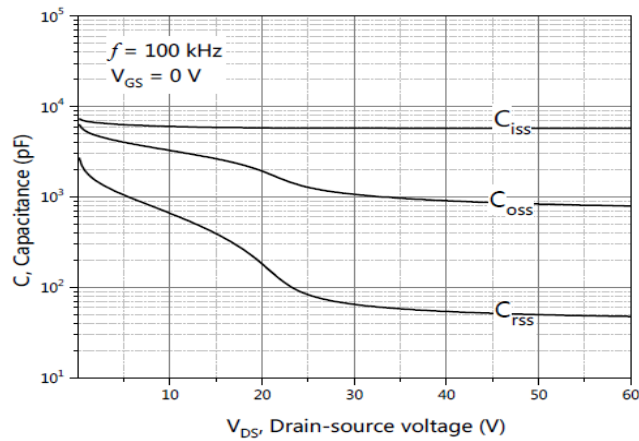


Figure3. Capacitance Characteristics

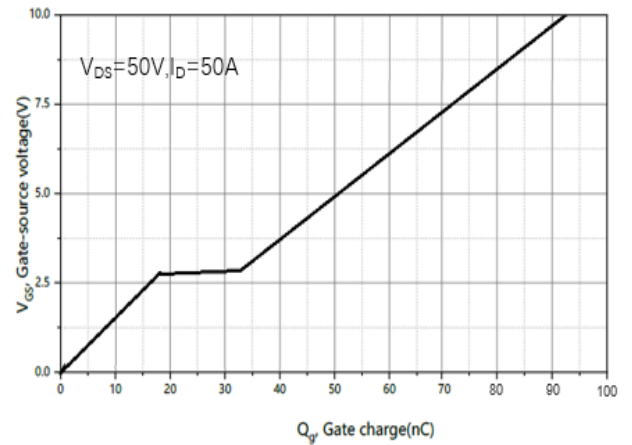


Figure4. Gate Charge

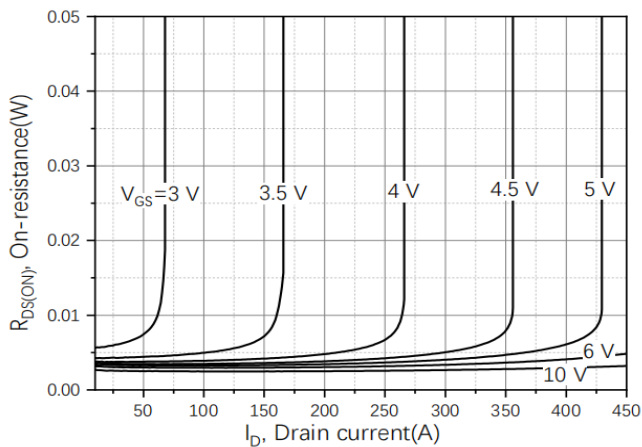


Figure5. Drain-Source on Resistance

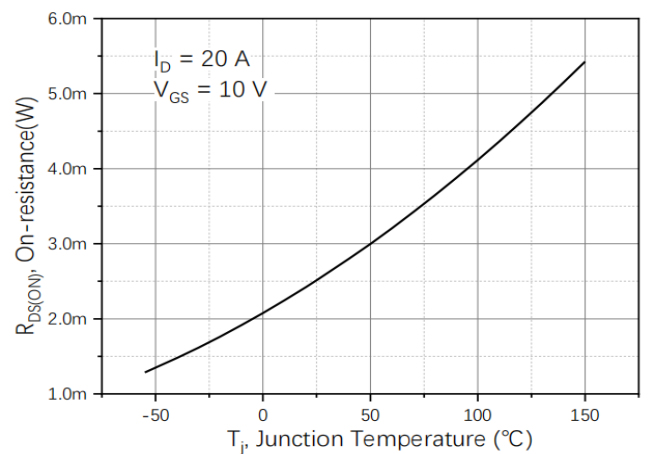


Figure6. Drain-Source on Resistance

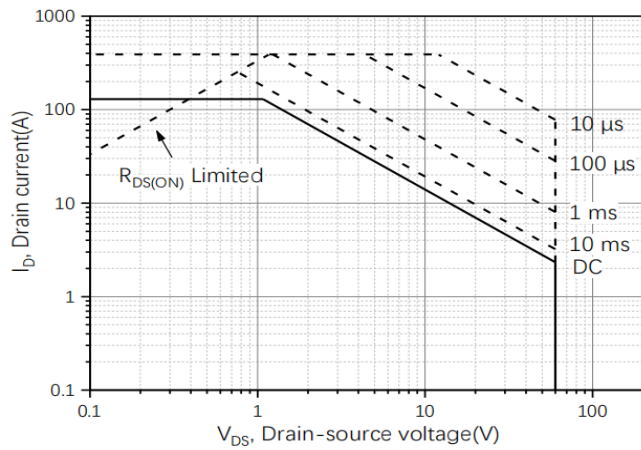


Figure 7. Safe Operation Area

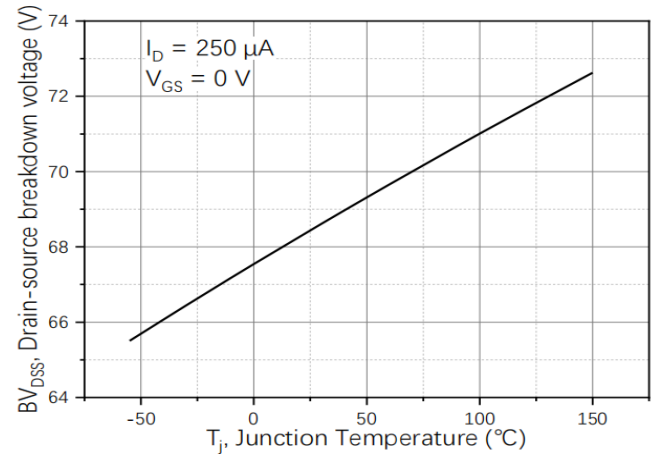


Figure 8. Drain-source breakdown voltage

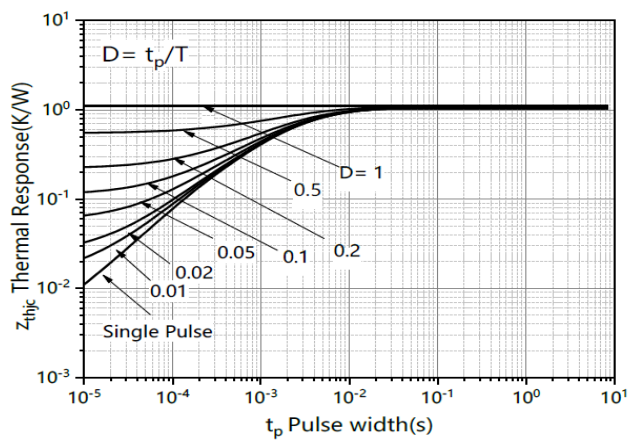


Figure 9. Transient thermal impedance

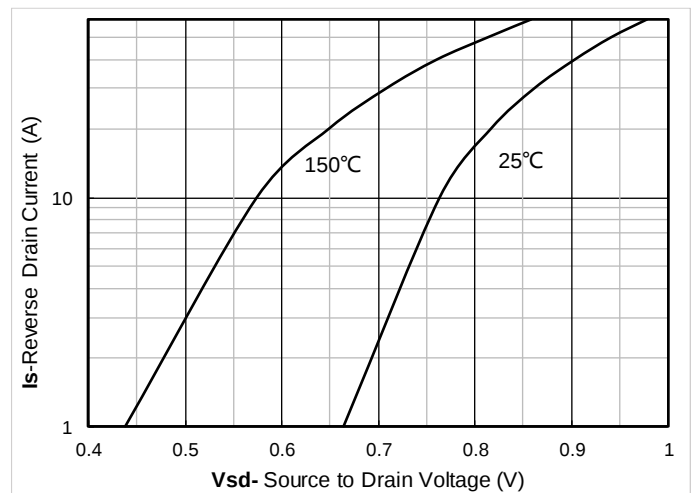


Figure 10. Forward characteristics of reverse diode

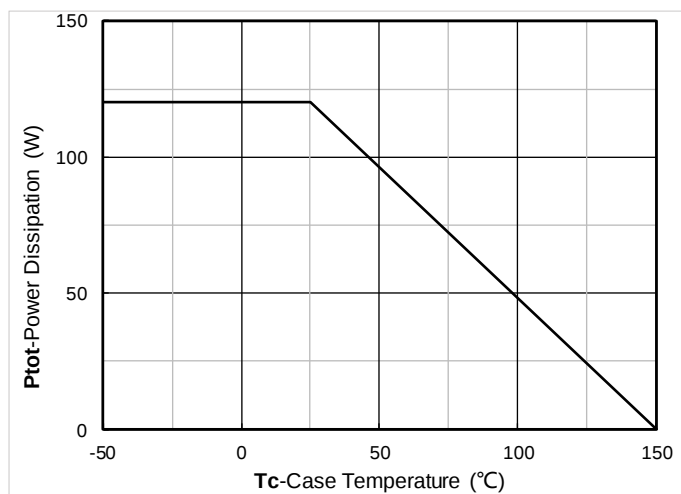


Figure 11. Power dissipation

■ Test circuits and waveforms

Figure A: Gate Charge Test Circuit & Waveforms

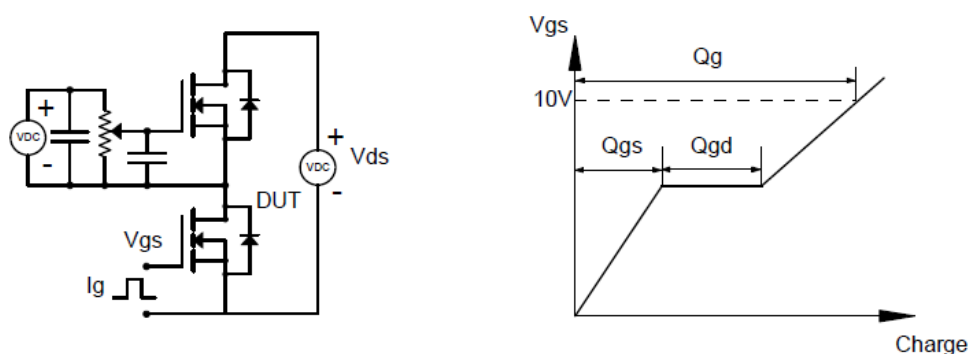


Figure B: Resistive Switching Test Circuit & Waveforms

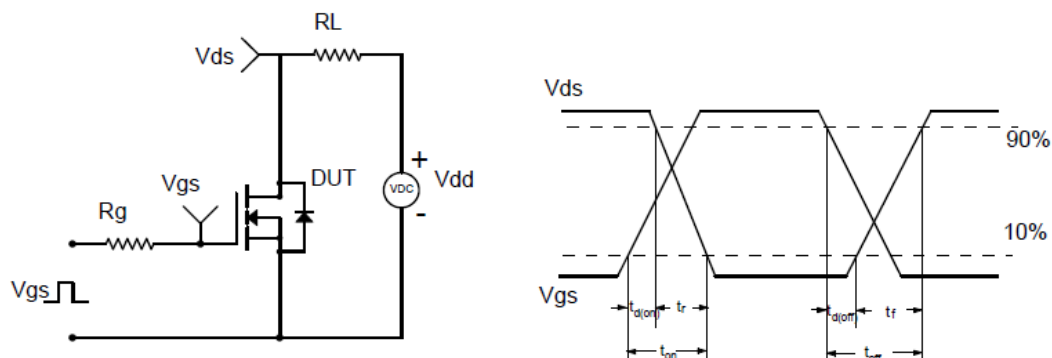


Figure C: Unclamped Inductive Switching (UIS) Test

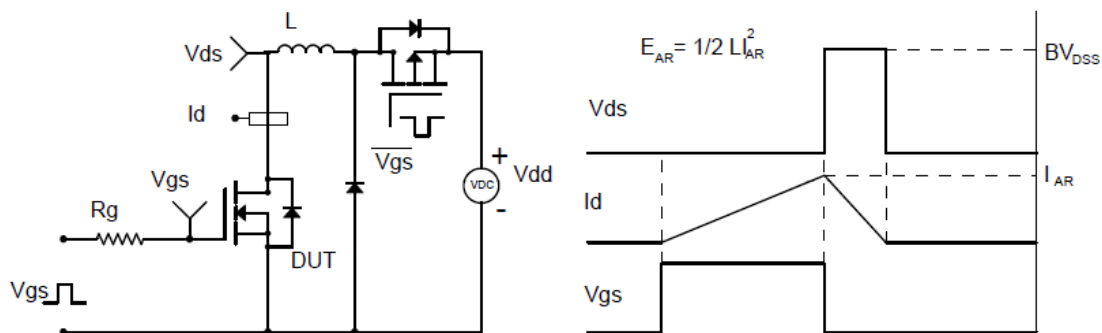
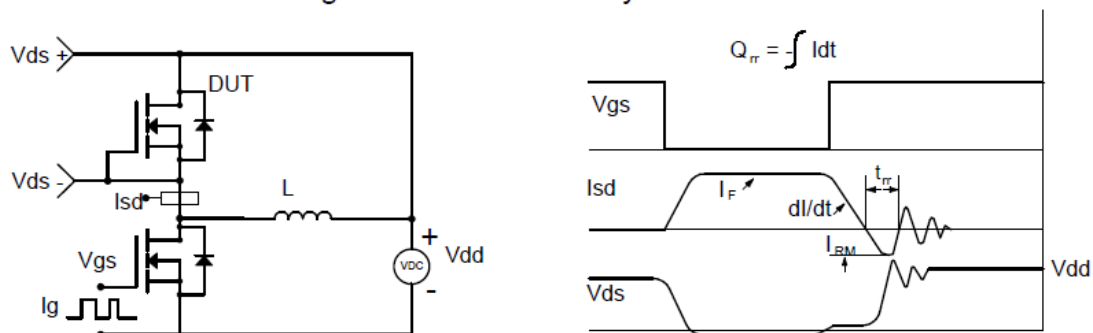
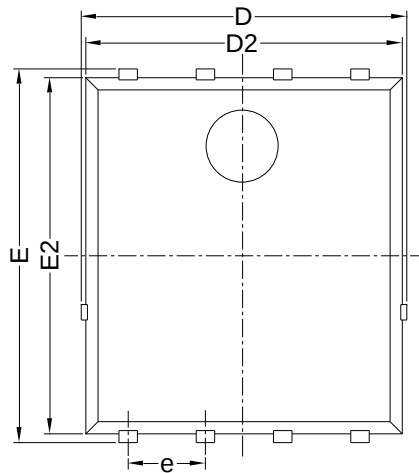


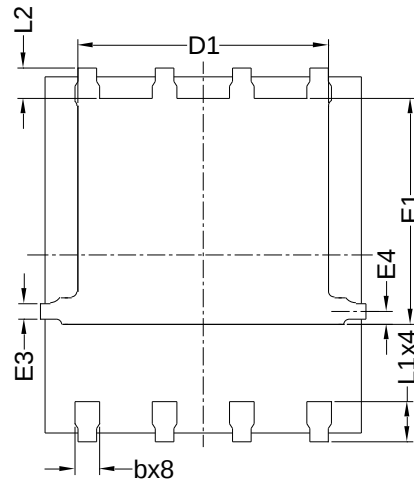
Figure D: Diode Recovery Test Circuit & Waveforms



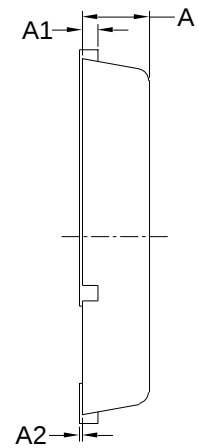
■ PDFN5060-8L-B-1.1MM Package Information



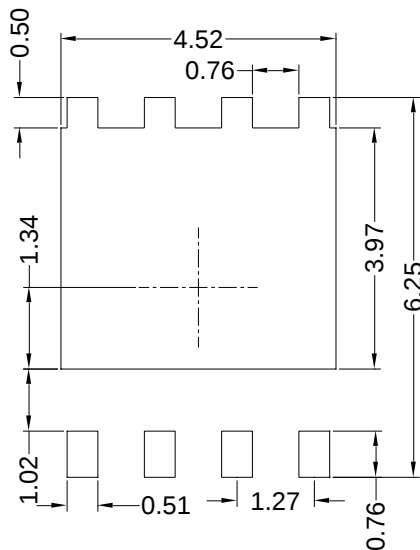
Top View
正面视图



Bottom View
背面视图



Side View
侧面视图



Suggested Solder Pad Layout
Top View

SYMBOL	MILLIMETER		
	MIN	NOM	MAX
D	5.15	5.35	5.55
E	5.95	6.15	6.35
A	1.00	1.10	1.20
A1	0.254 BSC		
A2			0.10
D1	3.92	4.12	4.32
E1	3.52	3.72	3.92
D2	5.00	5.20	5.40
E2	5.66	5.86	6.06
E3	0.254 REF		
E4	0.21 REF		
L1	0.56	0.66	0.76
L2	0.50 BSC		
b	0.31	0.41	0.51
e	1.27 BSC		

Note:

1. Controlling dimension: in millimeters.
2. General tolerance: ± 0.10 mm.
3. The pad layout is for reference purposes only.

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